TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

GT8G133

Strobe Flash Applications

- Compact and Thin (TSSOP-8) package
- Enhancement-mode
- 4-V gate drive voltage: $V_{GE} = 4.0 \text{ V (min)}$ (@IC = 150 A)
- Peak collector current: IC = 150 A (max)

Absolute Maximum Ratings (Ta = 25°C)

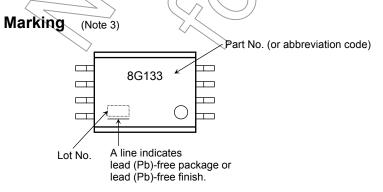
Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	400		
Gate-emitter voltage	DC	V _{GES}	± 6	$\langle \gamma \rangle \wedge$	
	Pulse	V _{GES}	± 8	$(\lor /))$	
Collector current	Pulse (Note 1)	I _{CP}	150	A	
Collector power dissipation (t=10 s)	(Note 2a)	P _C (1)	1,4	\supset W	
	(Note 2b)	P _C (2)	0.6	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	_55~150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

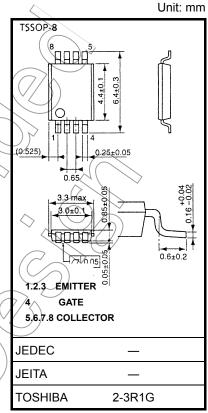
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal resistance , junction to ambient (t = 10 s) (Note2a)	R _{th (j-a)} (1)	114	°C/W
Thermal resistance , junction to ambient (t = 10 s) (Note2b)	R _{th (j-a)} (2)	208	°C/W

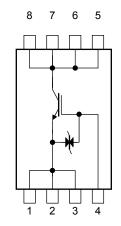


Note: For (Note 1), (Note 2a), (Note 2b) and (Note 3), Please refer to the next page.



Weight: 0.035 g (typ.)

Circuit Configuration

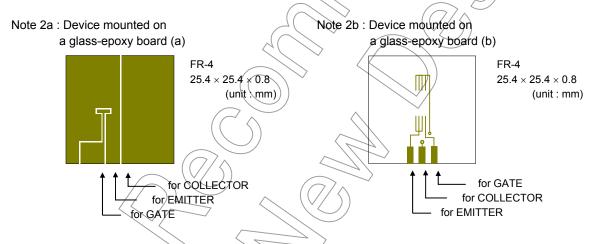


Electrical Characteristics (Ta = 25°C)

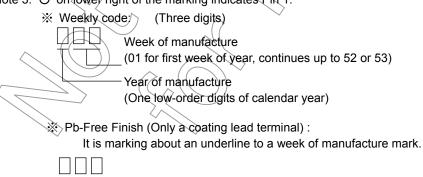
Chara	octeristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage curr	rent	I _{GES}	$V_{GE} = \pm 6 \text{ V}, V_{CE} = 0$	_	_	± 10	μА
Collector cut-off c	urrent	I _{CES}	V _{CE} = 400 V, V _{GE} = 0	_	_	10	μА
Gate-emitter cut-o	off voltage	V _{GE} (OFF)	I _C = 1 mA, V _{CE} = 5 V	0.7	1.05	1.4	٧
Collector-emitter	saturation voltage	V _{CE} (sat)	I _C = 150 A, V _{GE} = 4 V		2.9		٧
Input capacitance		C _{ies}	V _{CE} = 10 V, V _{GE} = 0, f = 1 MHz	(F	2500		pF
Switching time	Rise time	t _r	$\begin{array}{c} 4 \text{ V} \\ 0 \\ \end{array}$ $\begin{array}{c} 51 \Omega \\ \text{V}_{\text{IN}} \text{: } t_r \leq 100 \text{ ns} \\ \text{t}_f \leq 100 \text{ ns} \\ \text{Duty cycle} \leq 1\% \\ \end{array}$) \\	1.6		μs
	Turn-on time	t _{on}			1.7		
	Fall time	t _f		_	1.7	_	
	Turn-off time	t _{off}		- (2.0	\searrow	

Note

Note 1: Please use devices on condition that the junction temperature is below 150°C Repetitive rating: pulse width limited by maximum junction temperature.



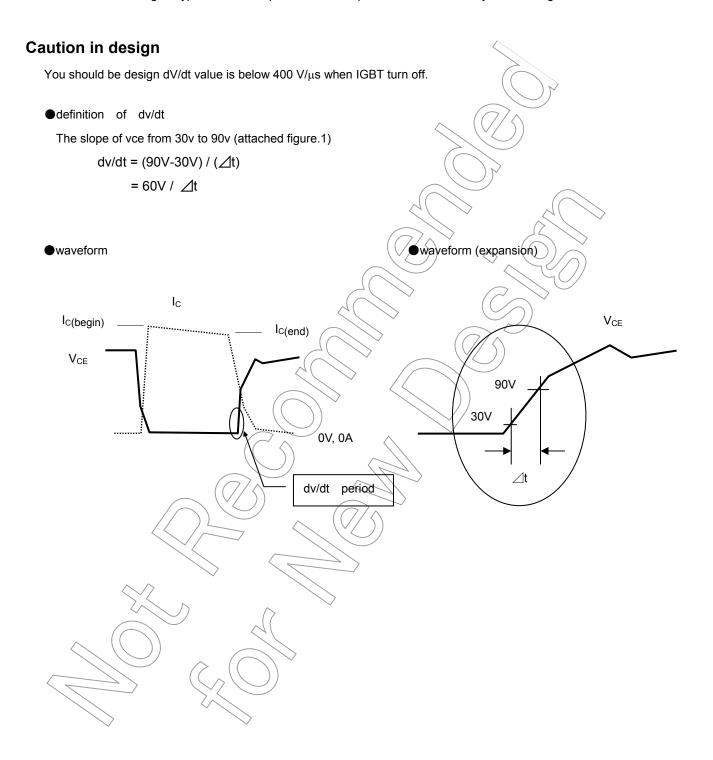
Note 3: O on lower right of the marking indicates Pin 1.



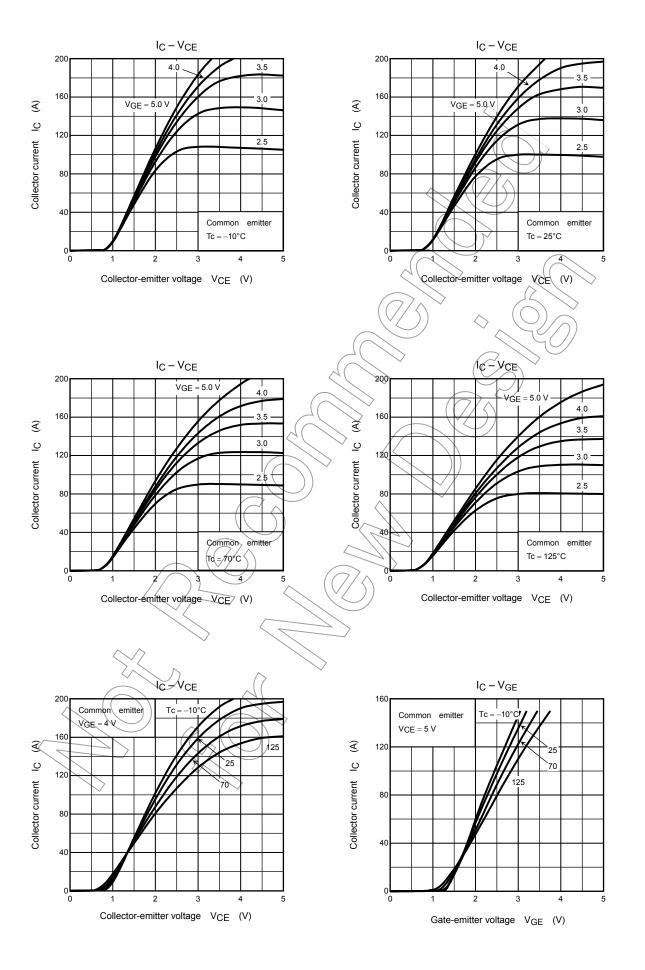
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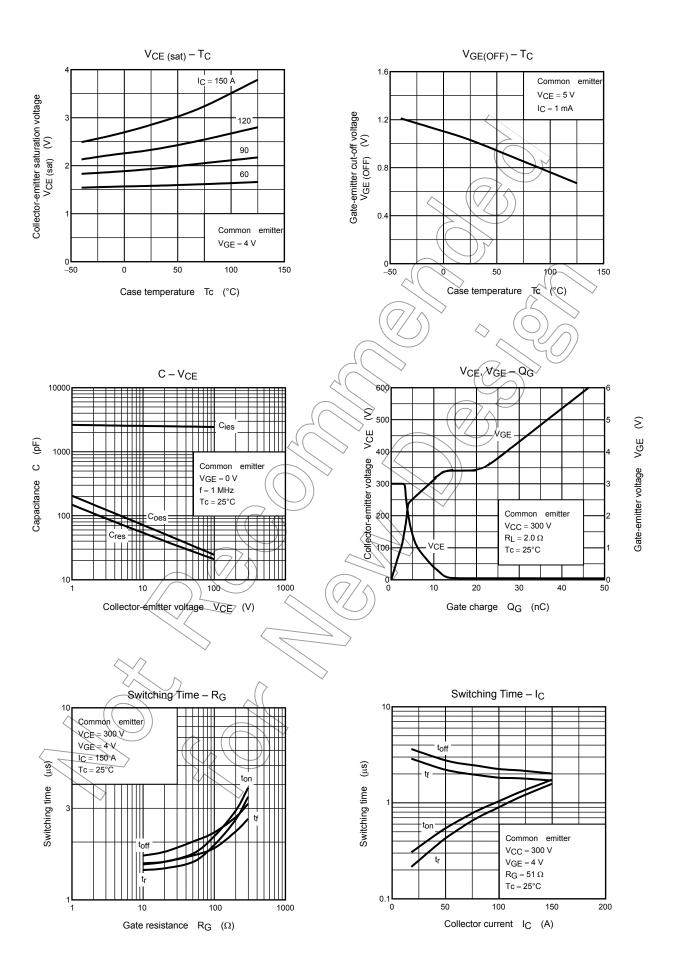
Caution on handling

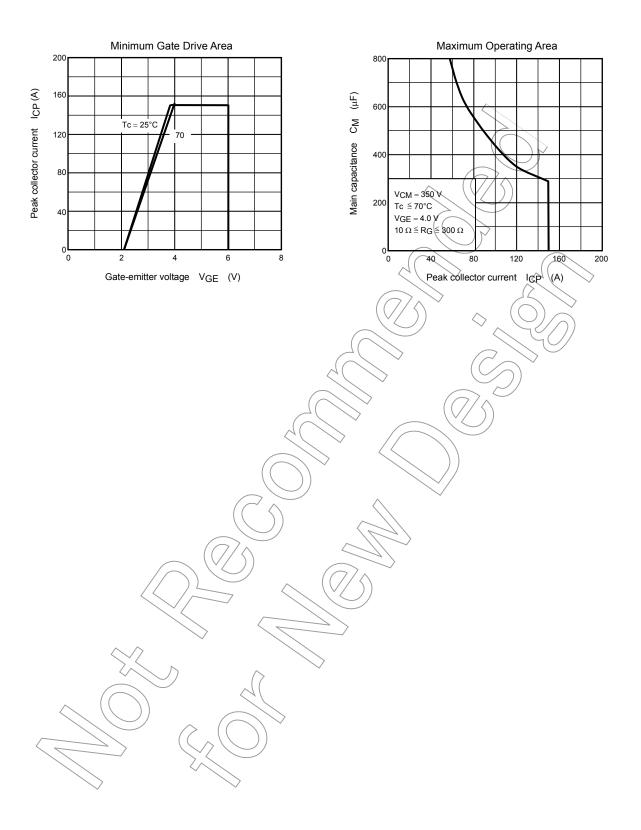
This device is MOS gate type. Therefore, please care of a protection from ESD in your handling.

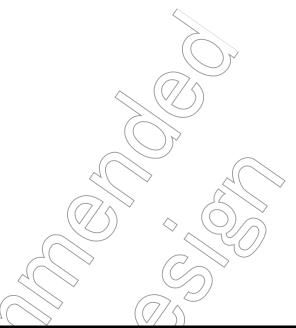


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